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Silicon PNP transistor in a SOT-89 Plastic Package.

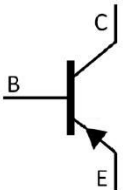
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Low voltage, high current, Complementary to BC868.

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Low voltage, high current applications.

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PIN1 Base PIN 2 Collector PIN 3 Emitter

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Marking	HCEC
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主要参数

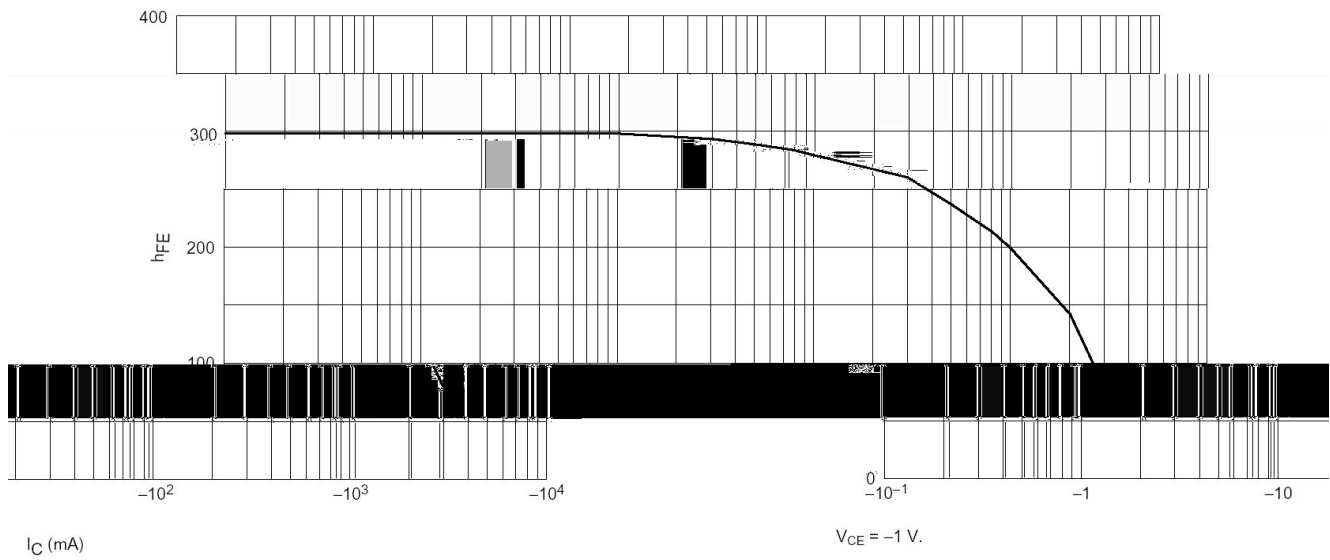
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Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-32	V
Collector to Emitter Voltage	V_{CEO}	-20	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current-Continuous	I_C	-1.0	A
Peak Collector Current	I_{CM}	-2.0	A
Peak Base Current	I_{BM}	-200	mA
Collector Power Dissipation	P_C	1.35	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

测试条件

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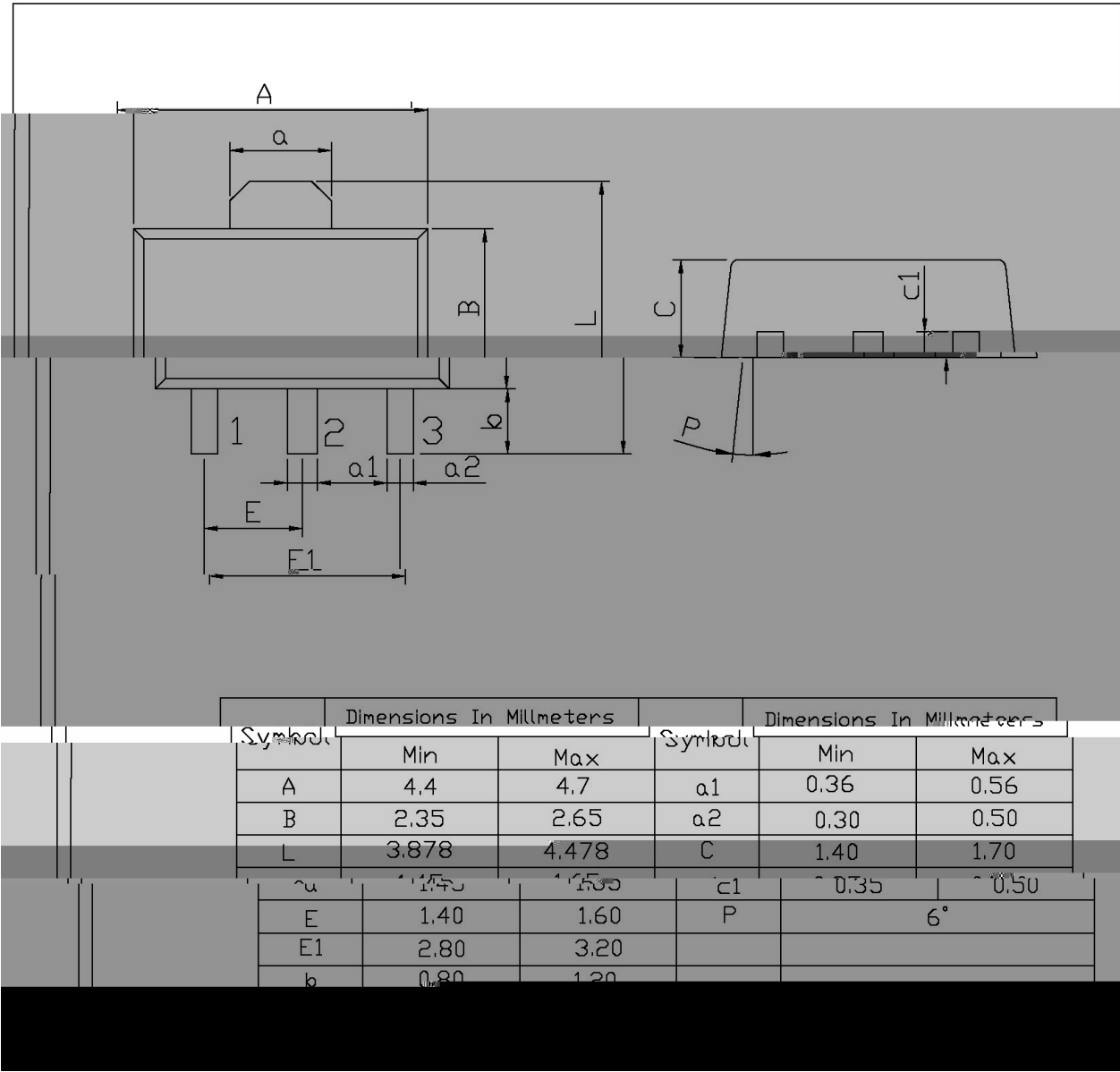
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-25V$ $I_E=0$			-0.1	μA
Emitter Base Cut-Off Current	I_{EBO}	$V_{EB}=-5.0V$ $I_C=0$			-0.1	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=-1.0V$ $I_C=-500mA$	100		375	
	$h_{FE(2)}$	$V_{CE}=-10V$ $I_C=-5.0mA$	50			
	$h_{FE(3)}$	$V_{CE}=-1.0V$ $I_C=-1.0A$	60			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-1.0A$ $I_B=-100mA$			-500	mV
Base to Emitter Voltage	$V_{BE(1)}$	$I_C=-5.0mA$ $V_{CE}=-10V$		-620		mV
	$V_{BE(2)}$	$I_C=-1.0A$ $V_{CE}=-1.0V$			-1.0	V
Transition Frequency	f_T	$V_{CE}=-5.0V$ $I_C=-10mA$ $f=100MHz$	40			MHz

h_{FE}

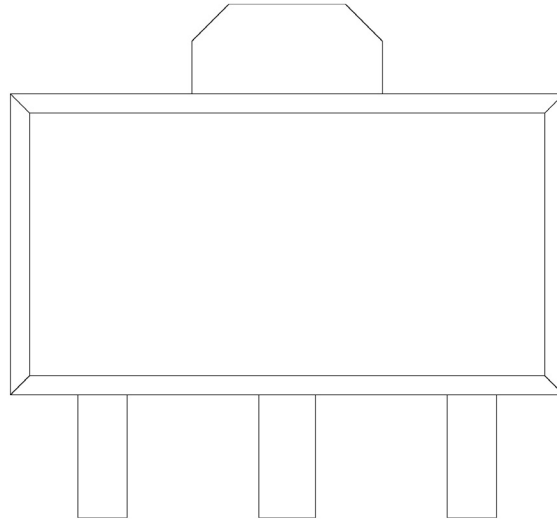
封装尺寸

SOT-89

单位：mm



1. 2



H

CEC

Note:

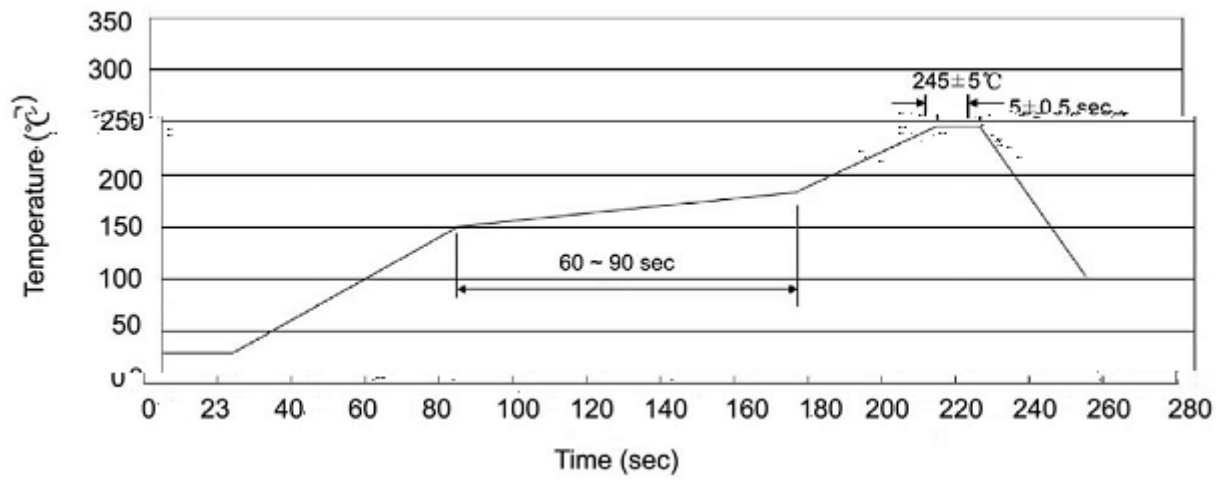
H: Company Code.

CEC: Product Type.

** : Lot No. Code, code change with Lot No.

温度曲线

Whp shudwxuh Suriloh i ru LU Uhior z Vroghulq j+Se0luhh,



Note:

- 1

25 150

60 90sec;

1.Preheating:25~150 , Time:60~90sec.
- 2

245 5

5 0.5sec;

2.Peak Temp.:245 5 , Duration:5 0.5sec.
- 3

2 10 /sec.

3. Cooling Speed: 2~10 /sec.

温度

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260 5

10 1 sec.

Temp.:260±5

Time:10±1 sec

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/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只 卷盘	卷盘 盒	只 盒	盒 箱	只 箱		盒	箱
						"		

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